



**FEATURES**

- Ideal for electron detection
- Large detection area
- 100% internal QE

Dimensions are in inch [metric] units.

**ELECTRO-OPTICAL CHARACTERISTICS AT 25°C**

| PARAMETERS                       | TEST CONDITIONS            | MIN  | TYP  | MAX  | UNITS           |
|----------------------------------|----------------------------|------|------|------|-----------------|
| Active Area                      | 10mm x 10mm                |      | 100  |      | mm <sup>2</sup> |
| Responsivity, $\mathcal{R}$      | @ 254nm, $V_R = 0V$        | 0.07 | 0.08 | 0.09 | A/W             |
| Shunt Resistance, $R_{sh}$       | $V_B = \pm 10mV$           | 20   |      |      | M-ohm           |
| Reverse Breakdown Voltage, $V_R$ | $I_R = 1\mu A$             |      | 10   |      | Volts           |
| Capacitance, C                   | $V_R = 0V$                 |      | 10   | 44   | nF              |
| Rise Time                        | $V_R = 0V, R_L = 50\Omega$ |      |      | 10   | usec            |

**THERMAL PARAMETERS**

| STORAGE AND OPERATING TEMPERATURE RANGE |                           |
|---|---------------------------|
| Ambient <sup>2</sup>                    | -10° TO 40°C <sup>2</sup> |
| Nitrogen or Vacuum                      | -20°C TO 80°C             |
| Maximum Junction Temperature            | 70°C                      |
| Lead Soldering Temperature <sup>1</sup> | 260°C                     |

<sup>1</sup>0.08" from case for 10 seconds.

<sup>2</sup>Temperatures exceeding these parameters may create Oxide growth on the active area.

Over time Responsivity to Low energy radiation and wavelengths below 150nm will Be Compromised.

Shipped with temporary cover to protect photodiode and wire bond. Review Opto Diode "Handling Precautions for IRD Detectors" prior to removing cover.

